

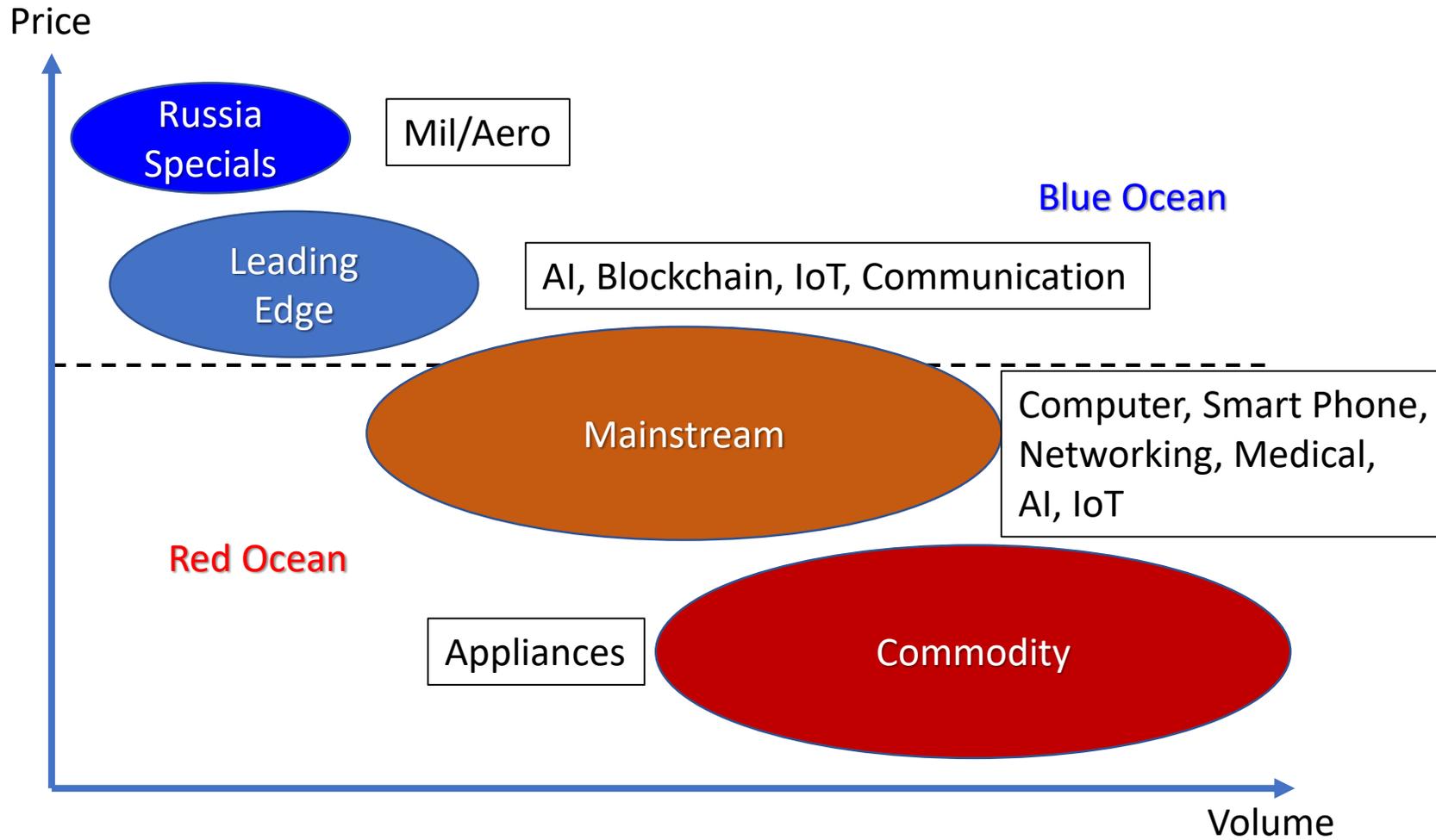


Libraries and Design IPs

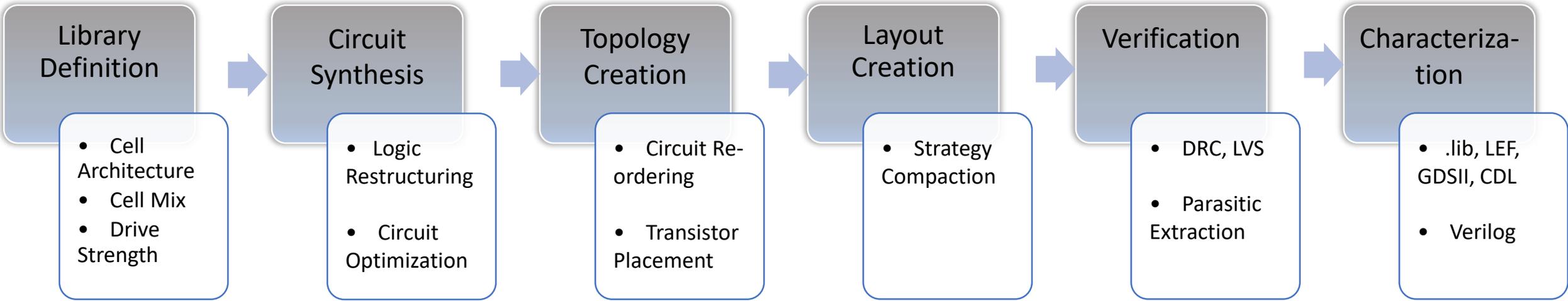
March 2019

Moscow

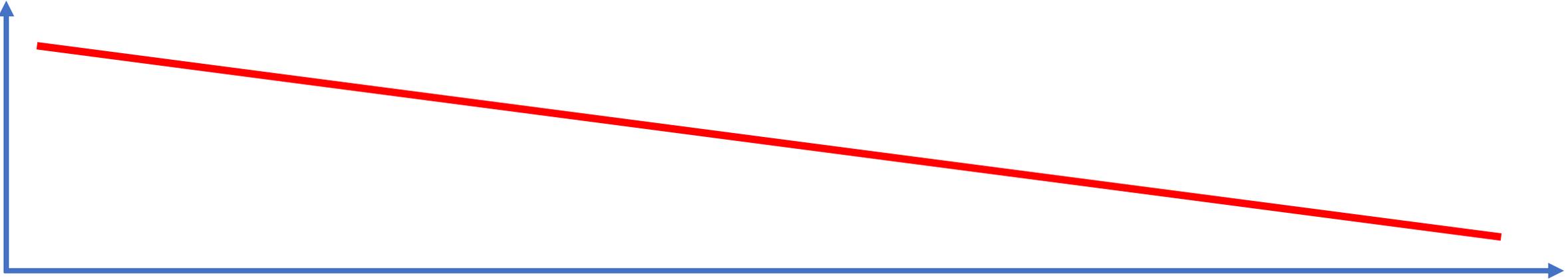
Product Position



Design Flow



1st time silicon success rate



Design Stages

Strategy of Libraries & IP selection

PW	FE
PRF	IP
Area	BE
Cost	INTG VRFY
	TEST
	PKG

- Readily Available IPs
 - It can help kick start the chip design and lead to shorter design cycles.
- Cheaper Price
 - Applying generic foundation IP will often be cheaper as compared to the costs associated with internal IP development, verification and (test-chip) characterization.
- Silicon Proven
 - Mature production proven IPs reduce risk.
- Quality (PPAC)
 - Select the IPs that fit your requirements in term of Power, Performance, Area and Cost.

Case Study #1 – Analog Block

PW	FE
	IP
PRF	BE
	INTG
Area	VRFY
	TEST
Cost	PKG

Spec	IX XXXX ADC	GXXX ADC	KA ADC
Process	Silterra 0.13um	GSMC 0.13um	Silterra 0.13um
VDD	3.3V / 1.2V	5.0V / 1.5V	3.3V / 1.2V
Conversation Rate	2MSPS	1MSPS	2MSPS
Bits	12	12	14
Area	0.31mm ²	0.32mm ²	0.28mm ²
Power	3.6mW @ 1MSPS	5mW @ 1MSPS	0.8mW w/o buffer @ 2MSPS 2.0mW w/ buffer @ 2MSPS 0.5mW w/o buffer @ 1MSPS 1.8mW w/ buffer @ 1MSPS
Input range	N/A	1.8V ~ 5.5V	2.7V ~ 3.6V
Input mode			
Temperature	-40°C ~ 85°C	-40°C ~ 85°C	-40°C ~ 125°C
Channel	16 (single-mode) 8 (diff-mode)	16 (single-mode)	16 (single-mode) 8 (diff-mode)
Input load	30pF	26pF	13pF (single-mode) 26pF (diff-mode)

Case Study #2 – Fundamental IP

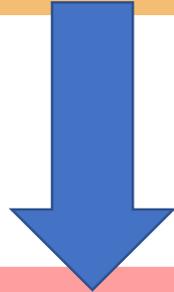
Spec Features	SXXXX GPIO#1	KA GPIO#1
Process Technology	Silterra C13G	Silterra C13G
I/O Standard	LVC MOS	LVC MOS
Bonding	Staggered	Inline
Size	Big (0.0141area ²)	Small (0.0065area ²)
ESD / LU Compliant	Yes	Yes
Special design: Power-on-control for crowbar current	No	Yes
Pass Issues: latch-up @ high	Yes	No
Pass Issues: ESD Failure	Yes	No

PW	FE
PRF	IP
	BE
Area	INTG
	VRFY
Cost	TEST
	PKG

Case Study #3 – Standard Cell Library

Power

Typical Original Standard Cell Design Window



Reduce 10% ~ 20% dynamic current
Reduce 30% ~ 40% static current

Monclova Standard Cell Library

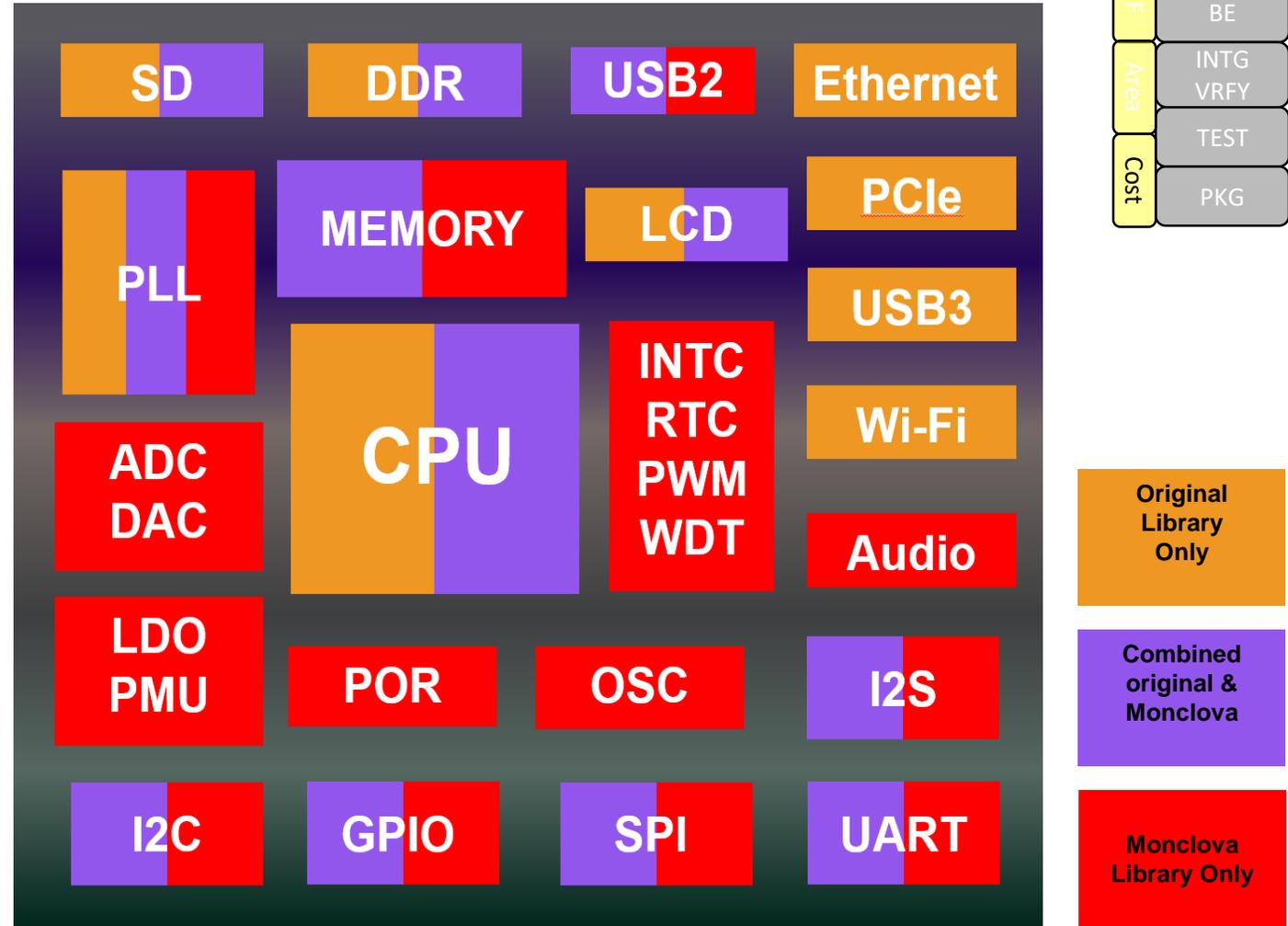
Typical ULP Cell Design Window

Speed

PW	FE
PRF	IP
Area	BE
Cost	INTG
	VRFY
	TEST
	PKG

Case Study #3 – Standard Cell Library

- Can mixed with others same process library

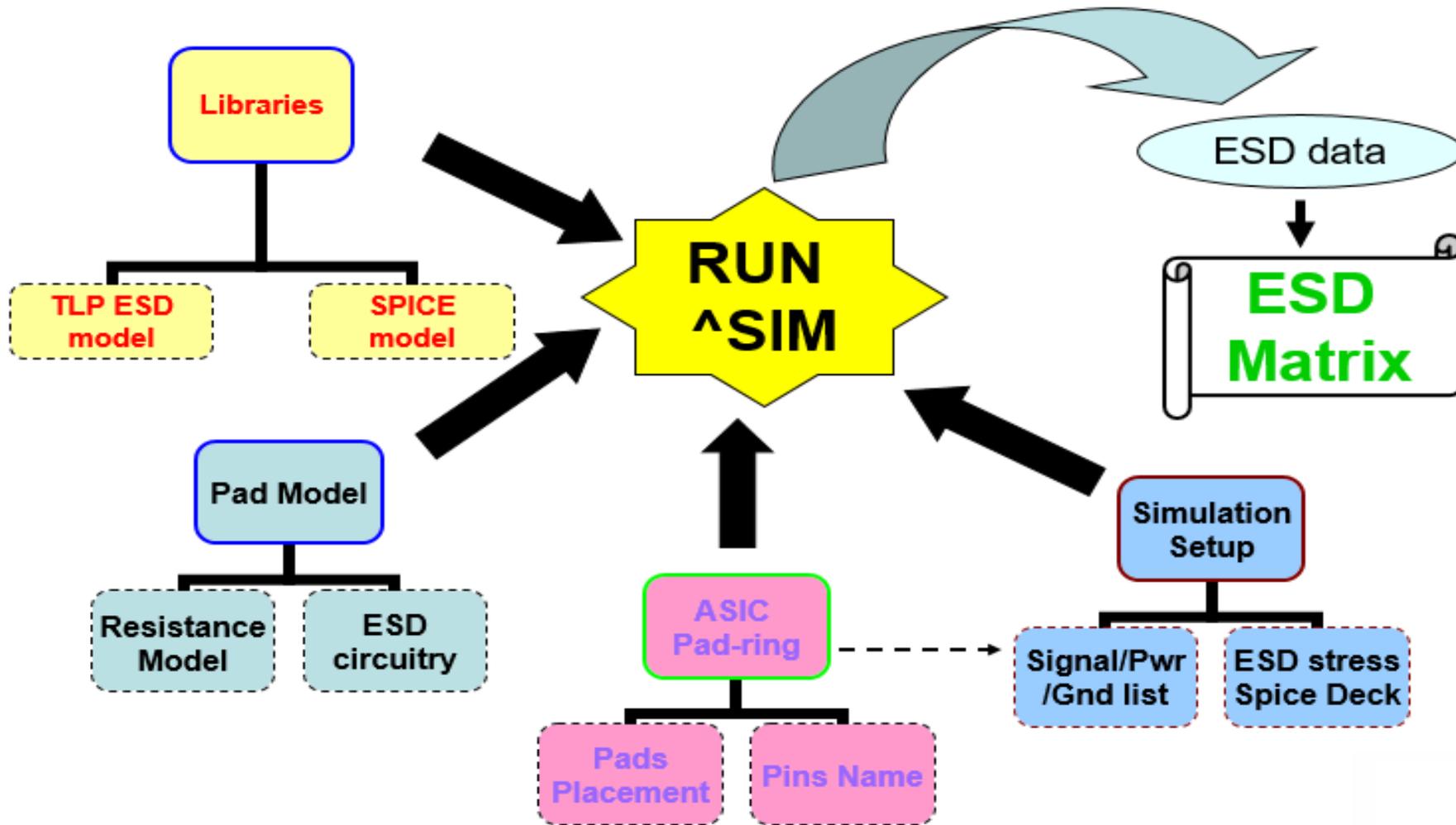


ESD / LU Design Challenges

- No specific EDA tool for ESD simulation
- Full Chip Pad Ring simulation take times to complete

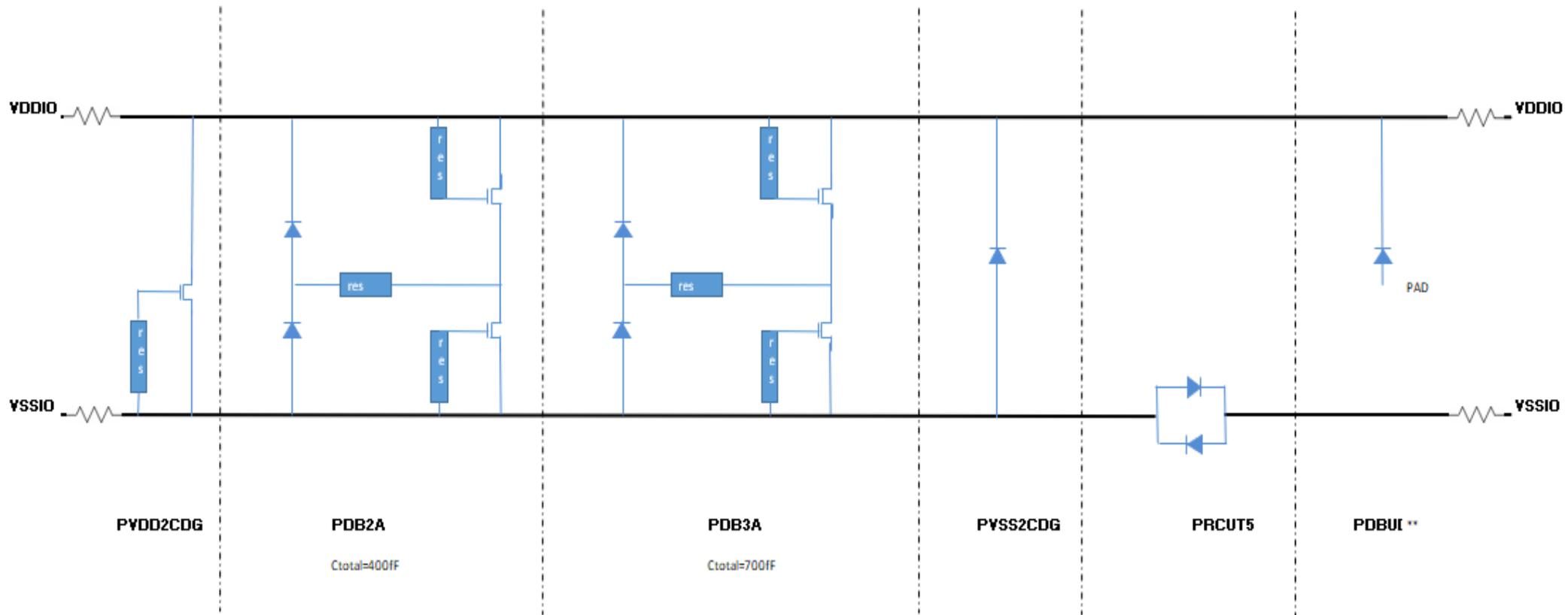
PW	FE
PRF	IP
BE	BE
Area	INTG VRFY
Cost	TEST
	PKG

Case Study 4 - ^Sim



PW	FE
PRF	IP
Area	BE
Cost	INTG
	VRFY
	TEST
	PKG

I/O Pad Modelling



PW	FE
PRF	IP
Area	BE
Cost	INTG
	VRFY
	TEST
	PKG

* Proposed customize cells for UMIC

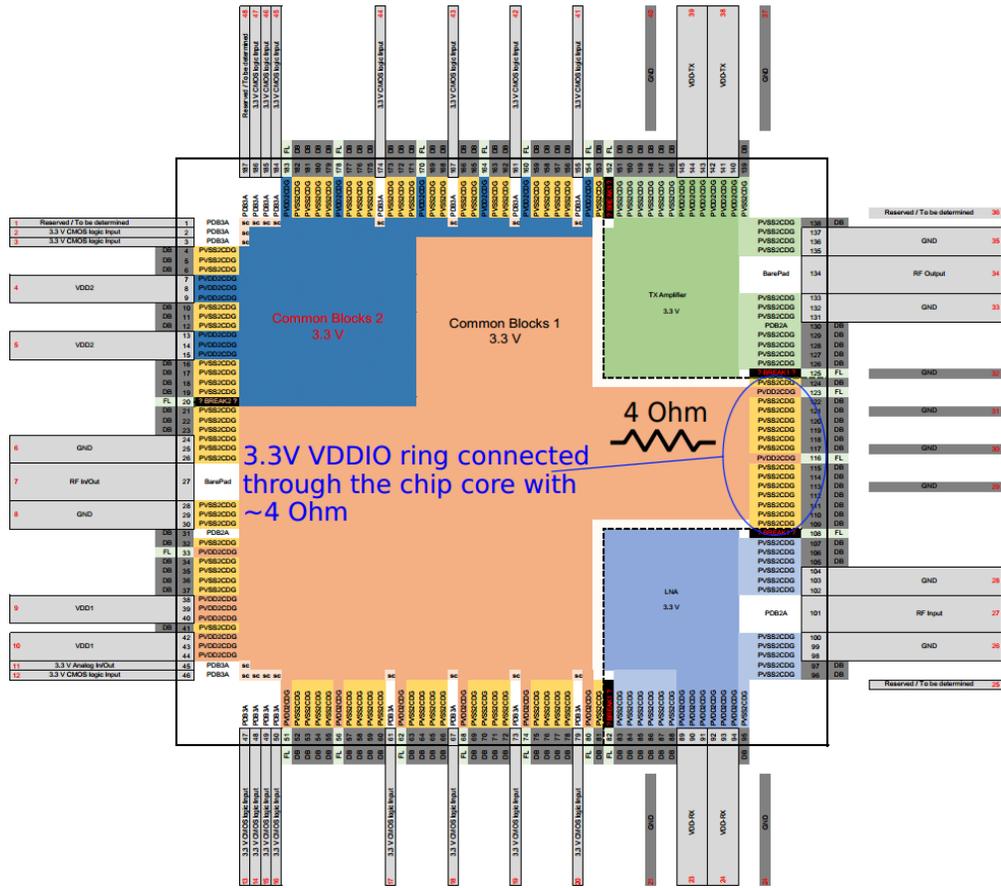
* POWER and GND Breakers cells will at 82, 108, 125, 152. (refer to SIRIUS_KeyAsicPADRing_07032018_v1_ea.pdf)

* Both side of PDB2A / PDB3A will have PRCUT5

** new added cell based on customer requested

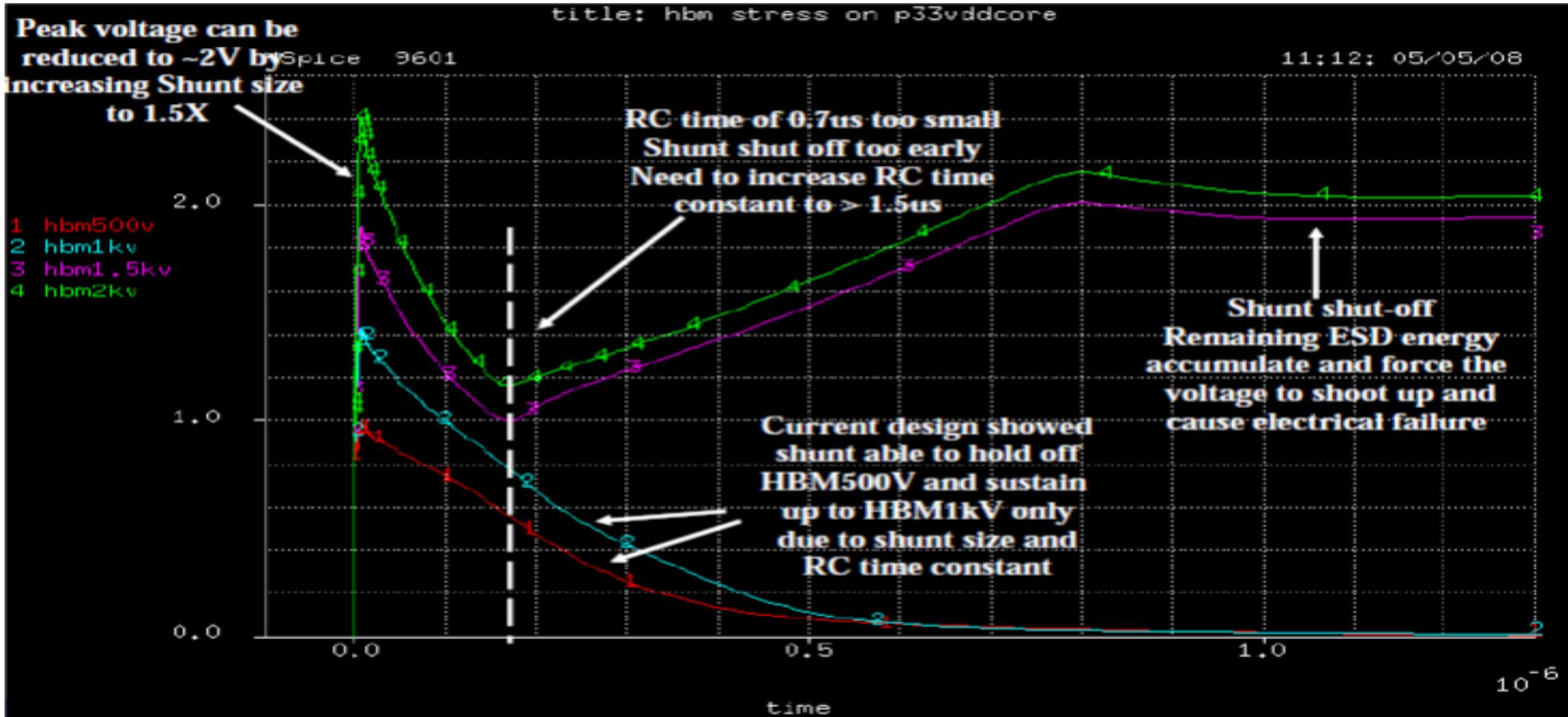
Pad Ring Modelling

- PW
 - PRF
 - Area
 - Cost
- FE
 - IP
 - BE
 - INTG VRFY
 - TEST
 - PKG



Pad#	Instance-Name	Cell-name	Side	Type	Loading	Notre
1	PDB3A		L	AI		
2	PDB3A		L	AI		
3	PDB3A		L	AI		
4	PVSS2CDG		L	power		
5	PVSS2CDG		L	power		
6	PVSS2CDG		L	power		
7	PVDD2CDG		L	power		
8	PVDD2CDG		L	power		
9	PVDD2CDG		L	power		
10	PVSS2CDG		L	power		
11	PVSS2CDG		L	power		
12	PVSS2CDG		L	power		
13	PVDD2CDG		L	power		
14	PVDD2CDG		L	power		
15	PVDD2CDG		L	power		
16	PVSS2CDG		L	power		
17	PVSS2CDG		L	power		
18	PVSS2CDG		L	power		
19	PVSS2CDG		L	power		
20	PRCUT3		L			cut only power bus
21	PVSS2CDG		L	power		
22	PVSS2CDG		L	power		
23	PVSS2CDG		L	power		
24	PVSS2CDG		L	power		
25	PVSS2CDG		L	power		
26	PVSS2CDG		L	power		
27	BarePad		L	AI		no esd? current library have no barepad cell, 20-Mar, will use PDRUD
28	PVSS2CDG		L	power		
29	PVSS2CDG		L	power		
30	PVSS2CDG		L	power		
31	PDB2A		L			Can't use with this setting; 22-Mar: PAD core part will used, refer to sheet proposal
32	PVSS2CDG		L	power		
33	PVDD2CDG		L	power		
34	PVSS2CDG		L	power		
35	PVSS2CDG		L	power		
36	PVSS2CDG		L	power		
37	PVSS2CDG		L	power		
38	PVDD2CDG		L	power		
39	PVDD2CDG		L	power		

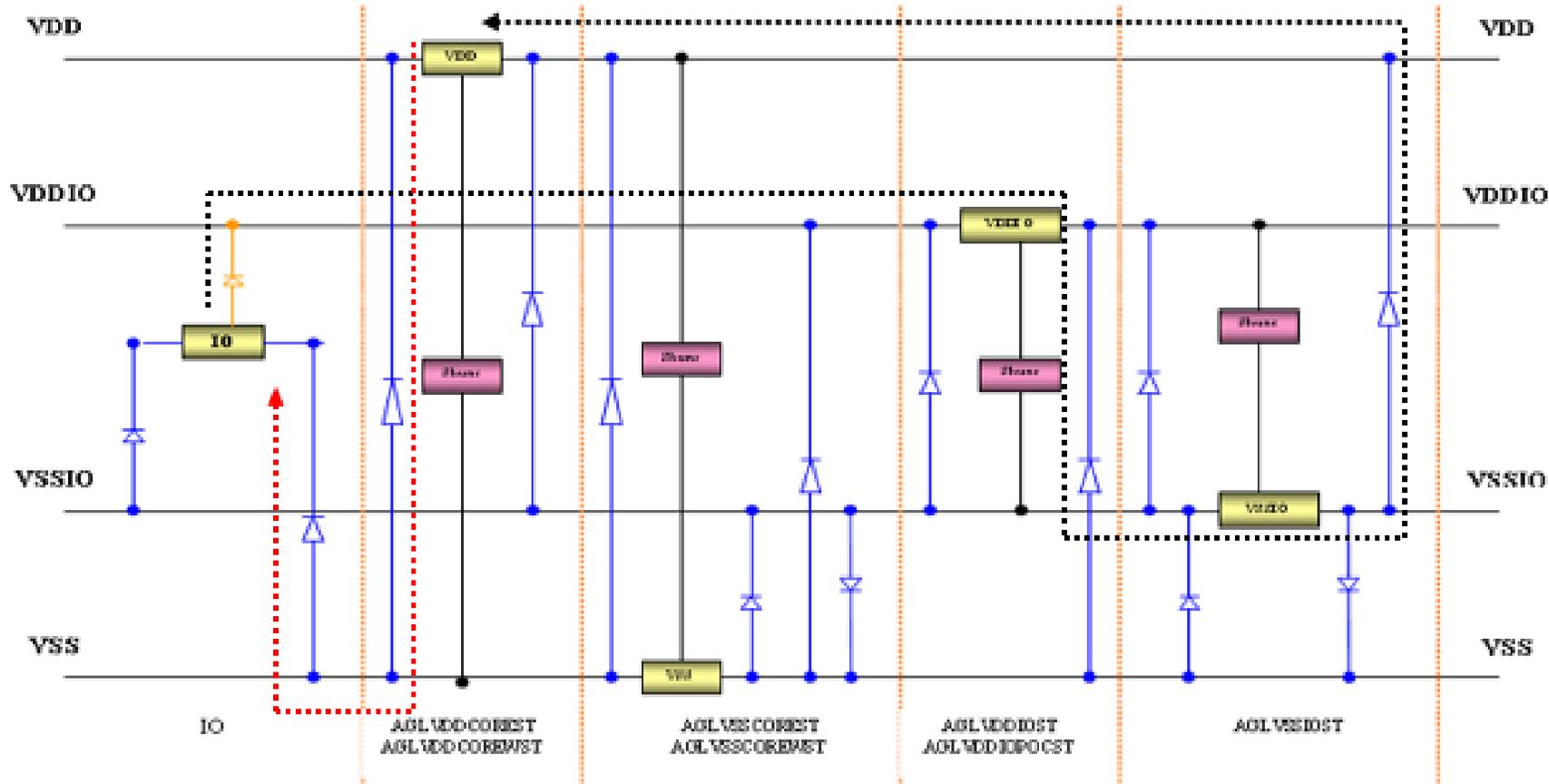
^Sim Simulation



PW	FE
PRF	IP
Area	BE
Cost	INTG
	VRFY
	TEST
	PKG

Analysis

ESD Scheme for Grill2 (Power Pads)



PW	FE
PRF	IP
Area	BE
Cost	INTG
	VRFY
	TEST
	PKG

Pins(+) Pins(-)	One IO
VDD	4.977
	-1.723

Zapping Voltage : 2kV HBM model

- 8V IO-shunt(5V) + 2 diode(2V) + IR drop(1V)
- 4V Core-shunt(2V) + 1 diode(1V) + IR drop(1V)

ESD Matrix

PW	FE
	IP
PRF	BE
	INTG
Area	VRFY
	TEST
Cost	PKG

BROOM2 ESD MATRIX															1st March Ying Poh		
<i>Zapping Voltage : 2kV HBM model</i>																	
	VDD	VSS	VDDIO	VSSIO	VDDIO	VSSIO	VDDIO	VSSIO	VDDIO	VSSIO	XYDD	VSSIO	VDD	VDDA	VSSA		
					DDR	DDR	USBD	USBD	USBD	USBD	OSC	OSC	PLL	PLL	PLL		
VDD	7.977															VDD	
	-1.723																
VSS	7.464	0.826														VSS	
	-1.106	-0.729															
VDDIO	8.42	1.579	1.132													VDDIO	
	-2.763	-2.271	-1.951														
VSSIO	8.371	1.539	1.084	2.663												VSSIO	
	-1.951	-1.35	-1.09	-0.731													
VDDIO	8.691	2.016	1.84	3.482	2.165											VDDIO	
DDR	-3.354	-2.836	-2.684	-3.166	-3.158											DDR	
VSSIO	8.666	1.995	1.818	3.462	2.147	2.72										VSSIO	
DDR	-2.346	-1.858	-1.675	-2.159	-2.151	-0.746										DDR	
VDDIO	9.313	2.296	2.135	4.452	2.596	4.02	2.539									VDDIO	
USBD	-6.767	-6.038	-5.88	-6.558	-6.511	-6.425	-6.399									USBD	
VSSIO	9.283	2.267	2.105	4.418	2.561	3.983	2.502	3.969								VSSIO	
USBD	-2.993	-2.271	-2.116	-2.791	-2.744	-2.655	-2.629	-0.767								USBD	
XYDD	9.244	2.296	2.086	4.435	2.587	4.049	2.559	5.288	1.58							XYDD	
OSC	-7.803	-7.075	-6.919	-7.599	-7.553	-7.48	-7.453	-6.272	-6.336							OSC	
VSSIO	9.086	2.155	1.939	4.299	2.453	3.937	2.44	5.282	1.574	6.253						VSSIO	
OSC	-2.778	-2.094	-1.927	-2.601	-2.564	-2.542	-2.517	-1.529	-1.591	-0.87						OSC	
VDD	9.304	2.294	2.08	4.442	2.601	4.121	2.616	5.768	2.056	6.748	1.4					VDD	
PLL	-3.692	-2.984	-2.984	-3.508	-3.47	-3.458	-3.432	-2.647	-2.703	-2.633	-2.364					PLL	
VDDA	9.236	2.269	2.057	4.415	2.572	4.075	2.575	5.595	1.884	6.571	1.265	2.245				VDDA	
PLL	-6.039	-5.325	-5.173	-5.849	-5.806	-5.779	-2.753	-4.856	-4.913	-4.846	-4.618	-4.622				PLL	
VSSA	9.435	2.437	2.282	4.607	2.758	4.234	2.74	5.733	2.022	6.71	1.749	2.336	4.729			VSSA	
PLL	-2.742	-1.998	-1.998	-2.551	-2.509	-2.491	-2.465	-1.858	-1.906	-1.858	-1.64	-1.609	-1.465			PLL	
	VDD	VSS	VDDIO	VSSIO	VDDIO	VSSIO	VDDIO	VSSIO	VDDIO	VSSIO	XYDD	VSSIO	VDD	VDDA	VSSA		
					DDR	DDR	USBD	USBD	USBD	USBD	OSC	OSC	PLL	PLL	PLL		

Summary

- Always consider about reducing Power consumption, Better Performance, Minimize Area and Cheaper Cost during the early stage of design
- Robust ESD design is a MUST

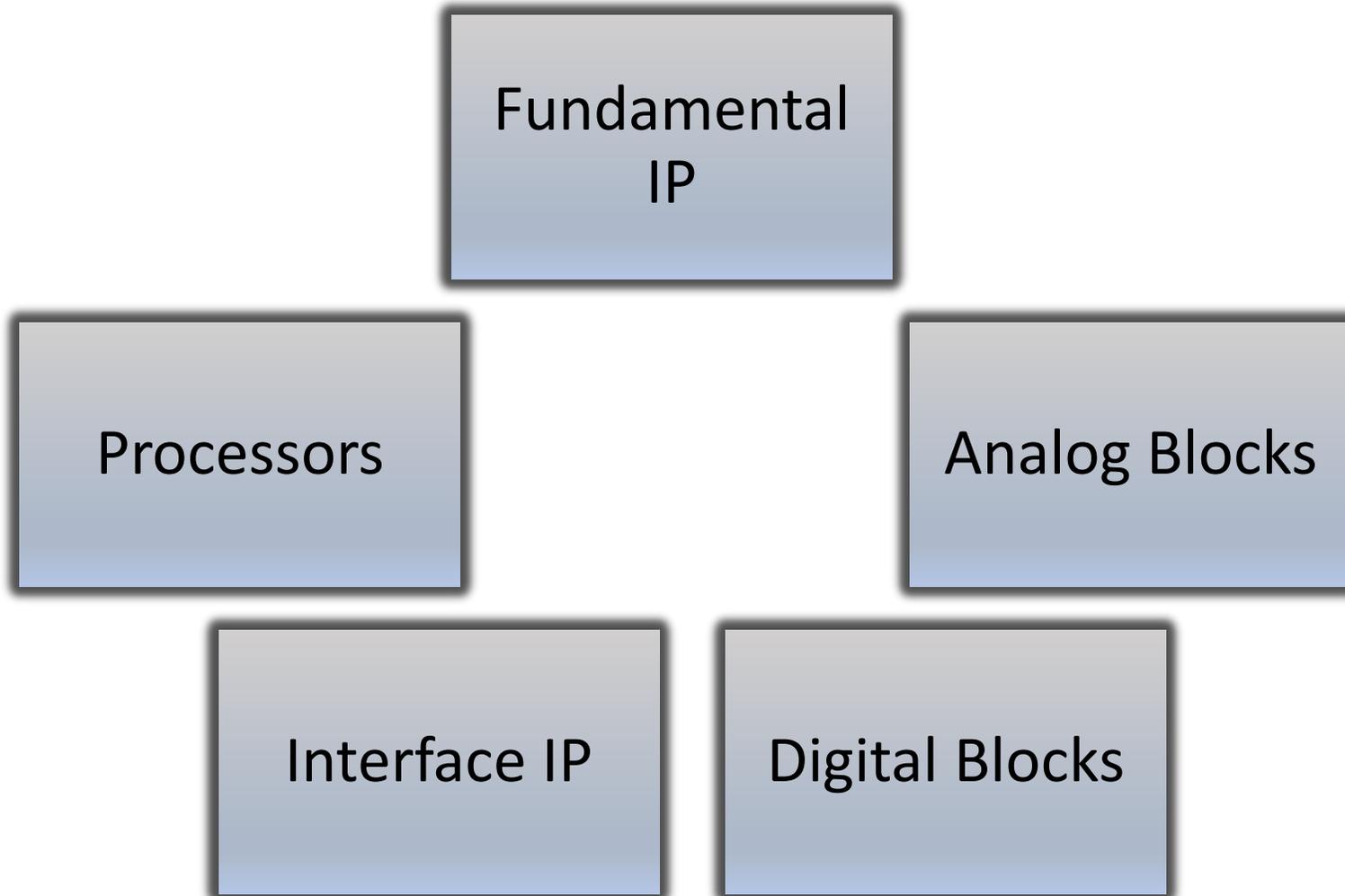
keyASIC

Thank you

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Appendix

Our IPs Portfolio



PW	FE
PRF	IP
Area	BE
Cost	INTG
	VRFY
	TEST
	PKG

Rich pool of silicon-proven IPs across different foundries & process nodes

Our IPs Portfolio

Fundamental IP

- Hybrid standard cell library for IoT & battery-powered application
- Memory (foundry-sponsored)
- General Purpose I/O & Special Purpose I/O
- Clock & oscillator (crystal, RC, RTC)
- Power management (DC-DC converter, regulator, LDO)
- PLL (frequency synthesizer, spread spectrum)

PW	FE
PRF	IP
Area	BE
Cost	INTG VRFY
	TEST
	PKG

Our IPs Portfolio

Analog Blocks

- SAR ADC (8-bit, 10-bit, 12-bit,14-bit)
- Current-steering DAC (8-bit, 10-bit, 12-bit)
- Audio CODEC (sigma-delta, low power, I2S interface)
- Programmable gain amplifier (PGA)
- LED driver

PW	FE
PRF	IP
Area	BE
Cost	INTG VRFY
	TEST
	PKG

Our IPs Portfolio

Digital Blocks

- UART/USART
- GPIO
- SPI/SSI
- WDT
- I2C
- I2S
- PWM
- Interrupt controller
- RTC
- JTAG
- Bus Matrix
- AMBA 2.0 & 3.0
- DMA controller
- AXI-APB bridge

PW	FE
PRF	IP
Area	BE
Cost	INTG VRFY
	TEST
	PKG

Our IPs Portfolio

Interface IP

- Ethernet PHY
- USB1.1 / 2.0 / 3.0
- PCIe Gen1 / Gen2
- SATA 1.0 / 2.0 (PHY)
- SerDes
- LVDS transceiver
- DDR2, DDR3/3L
- LPDDR2
- SD 2.0 & SD 3.0
- SDIO 2.0 & SDIO 3.0
- Controllers for NAND Flash, CF4.2, AC97 Audio, CMOS sensor interface, TFT/LCD driver interface, LCD image scaling, Infrared wireless serial

PW	FE
PRF	IP
Area	BE
Cost	INTG VRFY
	TEST
	PKG

Our IPs Portfolio

Processors

- 8051
- ARM926EJS
- ARM Cortex-M3

PW	FE
PRF	IP
Area	BE
Cost	INTG VRFY
	TEST
	PKG

We do have a rich pool of silicon-proven IPs across different foundries & process nodes not limited to the list here.

Using multi-channel-length approach is optimized for the wearable, mobile and IOT products

Achieve the power goal without changing of the process technology, design flow and redesign of the analog and harden IPs.

MONCLOVA 
low power standard cells library for IoT products

